

This listing of claims will replace all prior version, and listings, of claims in the application:

Listing of claims:

174. (currently amended) A method of controlling the conduction of a pair of isolation transistors in a sense amplifier responsive to an array, comprising:

rendering the pair of transistors conductive during a write operation with a control signal that is a boosted version of the voltage used by the array; and
rendering the pair of transistors nonconductive by removing said control signal.

175. (currently amended) The method of claim 174 wherein said ~~step of~~ rendering the pair of transistors conductive includes ~~the step of~~ rendering the transistors conductive with a control signal that is approximately a V_{th} higher than the voltage used by the array.

176. (currently amended) The method of claim 174 wherein said ~~step of~~ rendering the transistors conductive includes ~~the step of~~ rendering the transistors conductive with a control signal that enables the full voltage representative of a logic level one to be written to the array.

177. (currently amended) A method of controlling the conduction of at least one isolation transistor in a sense amplifier responsive to an array, comprising:

rendering the transistor conductive with a control signal that enables a full V_{cc} to be conducted by the isolation transistor during a write operation; and
rendering the transistor nonconductive by removing said control signal.

178. (currently amended) The method of claim 177 wherein said ~~step of~~ rendering the transistor conductive includes ~~the step of~~ rendering the transistor conductive with a control signal that is approximately a V_{th} higher than V_{cc} .

179. (previously added) A method of enabling a write to a memory array of the full voltage representative of a logic level one using a sense amplifier in which the sense amplifiers are located inside the isolation transistors, comprising:

rendering the isolation transistors conductive with a control signal that compensates for the voltage drop across the isolation transistors.

180. (currently amended) The method of claim 179 wherein said rendering ~~step~~ includes ~~the step of~~ rendering the isolation transistors conductive with a control signal that is approximately a V_{th} higher than the voltage used to represent a logic level one.

181. (previously added) The method of claim 180 wherein said control signal is approximately V_{th} plus V_{cc} .
